

## CLAIMS

What is claimed is:

1. A process for creating an electrically isolated electrode on a sidewall of a cavity in a base, the process comprising the steps of:
  - etching one or more trenches in a backside of the base;
  - forming a layer of insulating material on one or more sidewalls of one or more of the trenches;
  - forming a conductive layer on the layer of insulating material on one or more sidewalls of one or more of the trenches; and;
  - removing base material from a portion of the base bordered by the one or more trenches.
2. The process of claim 1, wherein the trenches are defined underneath a flap.
3. The process of claim 1, wherein the trench etch stops on an etch-stop layer.
4. The process of claim 1, wherein the conductive layer completely fills the trench.
5. The process of claim 1, wherein a layer of conducting material is also deposited on the backside of the base.
6. The process of claim 1, wherein the trench is formed using an anisotropic etch.
7. The process of claim 1, wherein the base is a crystalline material.

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1 8. The process of claim 1 wherein the trench is etched such  
2 that an orientation of the sidewall is defined by a  
3 crystal orientation of the base material.

1 9. The process of claim 8, wherein the base is composed of  
2 crystalline silicon having a <110> crystal orientation.

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